# DATA SHEET 種多邦,专业PCB打样工厂,24小时加急出货



# SILICON TRANSISTOR 2SC5181

### NPN EPITAXIAL SILICON TRANSISTOR IN ULTRA SUPER MINI-MOLD PACKAGE FOR LOW-NOISE MICROWAVE AMPLIFICATION

#### **FEATURES**

- Low current consumption and high gain  $|S_{21e}|^2 = 10.5 \text{ dB}_{TYP}$ . @ Vce = 2 V, Ic = 7 mA, f = 2 GHz  $|S_{21e}|^2 = 9.0 \text{ dB}_{TYP}$ . @VcE = 1 V, Ic = 5 mA, f = 2 GHz
- Ultra Super Mini-Mold package

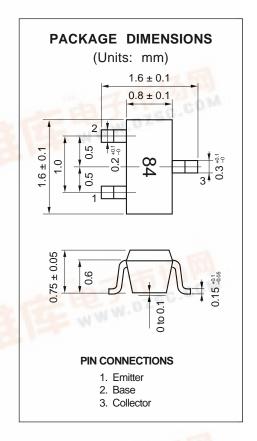
#### ORDERING INFORMATION

PART NUMBER	QUANTITY	ARRANGEMENT
2SC5181	50 units/box	Embossed tape, 8 mm wide, pin No. 3
2SC5181-T1	3 000 units/reel	(collector) facing the perforation

Contact your NEC sales representatives to order samples for evaluation (available in batches of 50).

#### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Collector to Base Voltage	Vсво	5	V
Collector to Emitter Voltage	VCEO	3	V
Emitter to Base Voltage	Vево	2	V
Collector Current	Ic	10	mA
Total Power Dissipation	Рт	30	mW
Junction Temperature	Tj	150	$^{\circ}C$
Storage Temperature	$T_{stg}$	-65 to +150	°C





### ELECTRICAL CHARACTERISTICS (TA = 25 $^{\circ}$ C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector Cutoff Current	Ісво			100	nA	Vcb = 5 V, IE = 0
Emitter Cutoff Current	ІЕВО			100	nA	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0
DC Current Gain	hfe	70		140		Vce = 2 V, Ic = 7 mA*1
Insertion Power Gain (1)	S <sub>21e</sub>   <sup>2</sup>	8.0	10.5		dB	VcE = 2 V, Ic = 7 mA, f = 2 GHz
Insertion Power Gain (2)	S <sub>21e</sub>   <sup>2</sup>	7.0	9.0		dB	Vce = 1 V, Ic = 5 mA, f = 2 GHz
Noise Figure (1)	NF		1.5	2.0	dB	VcE = 2 V, Ic = 3 mA, f = 2 GHz
Noise Figure (2)	NF		1.5	2.0	dB	Vce = 1 V, Ic = 3 mA, f = 2 GHz
Gain Bandwidth Product (1)	f⊤	10	13		GHz	VcE = 2 V, Ic = 7 mA, f = 2 GHz
Gain Bandwidth Product (2)	f⊤	8.5	12		GHz	Vce = 1 V, Ic = 5 mA, f = 2 GHz
Feedback Capacitance	Cre		0.4	0.6	pF	$V_{CB} = 2 \text{ V, I}_{E} = 0 \text{ mA, f} = 1 \text{ MHz}^{*2}$

- \*1. Measured with pulses: Pulse width  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %, pulsed
- \*2. Measured with a three-terminal bridge. The emitter and case terminal are connected to the guard terminal of the bridge.

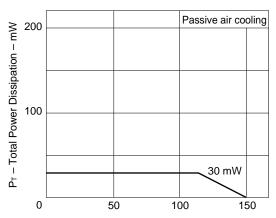
#### hfe Class

Class	FB
Marking	84
hfe	70 to 140

## **NEC**

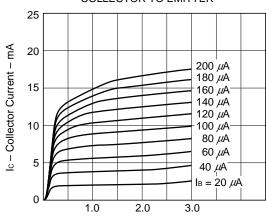
#### CHARACTERISTICS CURVES (TA = 25 °C)





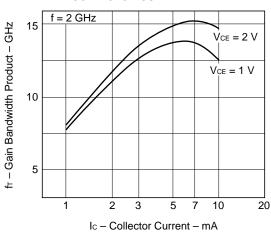
T<sub>A</sub> - Ambient Temperature - °C

## COLLECTOR CURRENT vs. COLLECTOR TO EMITTER

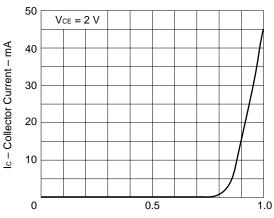


Vce - Collector to Emitter Voltage - V

## GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

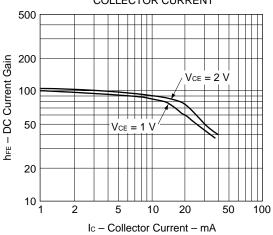


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

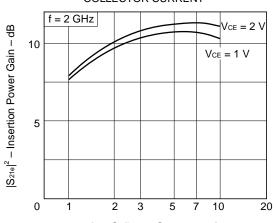


V<sub>BE</sub> – Base to Emitter Voltage – V

#### DC CURRENT GAIN vs. COLLECTOR CURRENT

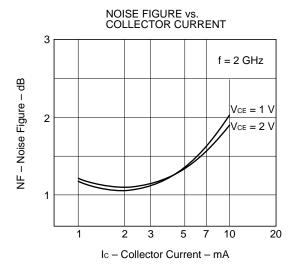


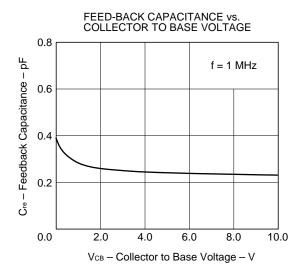
INSERTION POWER GAIN vs. COLLECTOR CURRENT



Ic - Collector Current - mA

**NEC** 2SC5181







#### **S-PARAMETERS**

S-PARAMETERS								
$V_{CE}$ = 1 V, Ic = 1 mA, $Z_{O}$ = 50 $\Omega$								
FREQUENCY	S	511	S2	21	S1:	2	SZ	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.892	-31.5	3.159	142.3	0.113	64.7	0.934	-25.9
800.00	0.795	-40.9	2.964	130.8	0.152	58.9	0.847	-32.1
1000.00	0.704	-50.9	2.762	119.7	0.180	53.0	0.759	-39.9
1200.00	0.653	-60.1	2.674	110.1	0.204	49.8	0.726	-47.4
1400.00	0.598	-66.6	2.590	103.0	0.228	45.9	0.688	-53.1
1600.00	0.524	-73.7	2.409	94.9	0.253	42.5	0.636	-58.2
1800.00	0.464	-80.6	2.285	87.2	0.265	41.3	0.575	-64.2
2000.00	0.415	-88.8	2.182	81.7	0.270	39.6	0.530	-68.9
2200.00	0.355	<b>-97.7</b>	2.032	74.6	0.278	35.7	0.495	-74.6
VcE = 1 V, Ic = 3 mA	A, Zo = 5	0 Ω						
FREQUENCY	S	311	S2	21	S1:	2	S2	22
		4410		4110	1440	4110	144.0	ANG
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.653	-48.4	6.121	124.0	0.095	59.6	0.754	-37.3
800.00	0.517	-59.5	5.199	111.4	0.123	55.7	0.629	-43.1
1000.00	0.422	-68.5	4.502	100.6	0.143	53.0	0.533	-49.5
1200.00	0.362	-76.1	4.084	92.8	0.165	53.5	0.493	-54.2
1400.00	0.301	-81.4	3.661	86.8	0.183	51.6	0.448	-57.6
1600.00	0.245	-88.0	3.279	79.5	0.204	50.1	0.411	-61.1
1800.00	0.209	-92.7	3.024	74.1	0.220	49.7	0.369	-66.7
2000.00 2200.00	0.175 0.132	-105.8 -121.6	2.796 2.535	70.4 64.5	0.230 0.244	50.0 46.8	0.334 0.311	-69.5 -75.0
Vce = 1 V, Ic = 3 mA			2.000	00	0.2	.0.0	0.0	7 0.0
FREQUENCY	S	511	S2	21	S1:	2	S2	22
MHz	MAG 0.514	ANG	MAG	ANG	MAG 0.082	ANG	MAG 0.648	ANG
600.00		-56.3 -66.9	7.156 5.830	115.3 103.5	0.082	57.8 57.0	0.648	-40.3 -44.6
800.00 1000.00	0.389 0.307	-00.9 -73.5	4.939	93.6	0.109	56.4	0.530 0.446	-44.6 -48.9
1200.00	0.307	-73.3 -79.7	4.391	86.9	0.151	56.4	0.440	-46.9 -52.5
1400.00	0.202	-7 9.7 -85.5	3.865	81.4	0.131	55.2	0.414	-52.5 -55.2
1600.00	0.202	-03.3 -91.8	3.440	74.7	0.173	53.8	0.347	-53.2 -58.4
1800.00	0.137	-96.2	3.155	70.1	0.190	53.5	0.347	-63.6
2000.00	0.108	-116.1	2.900	67.0	0.213	53.3	0.283	-65.6
2200.00	0.100	-142.5	2.614	61.5	0.241	50.7	0.268	–71.7
Vce = 1 V, Ic = 7 mA	A, Zo = 5	0 Ω						
FREQUENCY	S	311	S2	21	S1:	2	Sź	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.405	-61.9	7.590	109.4	0.077	59.1	0.570	-40.5
800.00	0.405	-01.9 -72.5	6.043	98.4	0.077	59.0	0.469	-40.5 -43.6
1000.00	0.303	-72.3 -78.2	5.059	89.2	0.101	57.9	0.409	-45.6 -46.6
1200.00	0.229	-76.2 -84.9	4.454	83.2	0.124	57.9 59.2	0.399	-40.6 -49.4
1400.00	0.164	-04.9 -91.4	3.886	78.0	0.143	59.2 57.6	0.374	-49.4 -51.8
1600.00	0.141	-91. <del>4</del> -98.8	3.455	71.6	0.109	56.2	0.322	-51.5 -54.5
1800.00	0.086	-104.3	3.162	67.6	0.210	55.3	0.290	-59.5
2000.00	0.071	-136.6	2.898	64.6	0.224	55.9	0.264	-61.4
2200.00	0.060	-174.6	2.606	59.4	0.237	52.7	0.249	-67.2

$V_{CE} = 1 \text{ V}, \text{ Ic} = 10 \text{ mA}, \text{ Zo} = 5$	Vce =	1 V.	Ic =	10 mA.	Zo =	50 Ω	2
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FREQUENCY	S	11	S2	21	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.324	-71.3	7.550	104.5	0.069	62.8	0.526	-39.4
800.00	0.232	-82.5	5.924	94.2	0.096	61.0	0.434	-40.5
1000.00	0.167	-89.5	4.927	85.5	0.119	59.7	0.375	-42.1
1200.00	0.128	-98.6	4.307	80.0	0.141	61.4	0.355	-44.8
1400.00	0.094	-110.3	3.740	74.9	0.165	60.6	0.335	-47.0
1600.00	0.067	-127.3	3.326	68.7	0.187	58.2	0.314	-49.2
1800.00	0.055	-140.2	3.041	64.9	0.207	57.6	0.283	-54.0
2000.00	0.068	-176.6	2.781	62.2	0.219	57.4	0.262	-56.1
2200.00	0.083	153.2	2.498	56.9	0.235	54.8	0.247	-62.0
VcE = 2 V, Ic = 1 m/	A, Zo = 5	0 Ω						
FREQUENCY	S	11	S2	21	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.901	-29.6	3.172	143.7	0.106	66.0	0.940	-24.4
800.00	0.811	-38.5	2.995	132.6	0.143	59.6	0.861	-30.3
1000.00	0.719	-47.8	2.797	121.7	0.172	55.0	0.778	-37.6
1200.00	0.671	-56.7	2.715	112.2	0.196	51.4	0.745	-45.0
1400.00	0.621	-62.9	2.646	105.3	0.220	47.9	0.712	-50.5
1600.00	0.549	-69.2	2.467	97.5	0.240	44.4	0.659	-55.0
1800.00	0.488	-75.6	2.343	89.8	0.255	43.6	0.601	-60.8
2000.00	0.438	-83.6	2.243	84.3	0.261	41.6	0.556	-65.6
2200.00	0.380	-91.1	2.095	77.3	0.268	37.8	0.522	-70.9
VcE = 2 V, Ic = 3 m/	A, Zo = 5	0 Ω						
FREQUENCY	S	11	S2	21	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.678	-44.9	6.256	125.7	0.088	60.5	0.778	-34.8
800.00	0.543	-55.3	5.350	113.4	0.114	56.1	0.656	-40.4
1000.00	0.447	-63.1	4.650	102.7	0.137	54.8	0.563	-46.1
1200.00	0.388	-69.9	4.225	94.8	0.157	54.2	0.519	-50.7
1400.00	0.325	-74.0	3.809	88.9	0.176	53.1	0.481	-54.5
1600.00	0.270	-78.9	3.408	81.8	0.195	51.3	0.441	-57.3
1800.00	0.231	-82.5	3.144	76.3	0.214	51.5	0.397	-62.3
2000.00	0.193	-93.2	2.918	72.7	0.223	51.1	0.363	-65.0
2200.00	0.148	-103.1	2.647	66.8	0.236	48.8	0.343	-70.0

$V_{CE} = 2 \text{ V}, \text{ Ic} = 5 \text{ mA}, \text{ Zo}$	= 5	$50~\Omega$
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FREQUENCY	S	11	S2	<u>!</u> 1	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.539	-51.7	7.390	117.1	0.080	61.7	0.676	-37.8
800.00	0.415	-61.1	6.057	105.3	0.103	58.5	0.560	-41.6
1000.00	0.332	-66.2	5.136	95.5	0.125	57.5	0.478	-45.6
1200.00	0.280	-71.9	4.579	88.7	0.146	58.5	0.445	-49.2
1400.00	0.228	-74.8	4.043	83.3	0.168	57.3	0.413	-51.6
1600.00	0.183	-78.2	3.597	76.8	0.187	55.4	0.383	-54.0
1800.00	0.157	-80.9	3.298	72.2	0.207	55.4	0.345	-58.9
2000.00	0.123	-95.6	3.042	69.1	0.218	55.5	0.317	-61.2
2200.00	0.084	-108.3	2.746	63.7	0.232	52.6	0.301	-66.0
VcE = 2 V, Ic = 7 mA	A, Zo = 5	0 Ω						
FREQUENCY	S	11	S2	.1	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.442	-56.3	7.920	111.3	0.070	63.0	0.610	-38.1
800.00	0.331	-65.1	6.345	100.3	0.097	59.0	0.507	-40.7
1000.00	0.257	-67.8	5.311	91.1	0.118	57.7	0.434	-43.4
1200.00	0.213	-73.1	4.689	85.1	0.141	60.4	0.407	-45.9
1400.00	0.168	-74.5	4.103	80.1	0.162	59.5	0.386	-48.0
1600.00	0.132	-77.3	3.643	73.8	0.184	58.3	0.359	-50.5
1800.00	0.110	-79.7	3.335	69.8	0.204	57.4	0.323	-54.8
2000.00	0.081	-99.2	3.065	66.9	0.214	57.5	0.301	-56.9
2200.00	0.048	-123.7	2.760	61.7	0.231	54.8	0.286	-62.3
VcE = 2 V, Ic = 10 m	nA, Zo =	50 Ω						
FREQUENCY	S	11	S2	<u>.</u> 1	S12	2	S2	22
MHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
600.00	0.358	-60.7	8.135	106.8	0.068	61.8	0.565	-36.5
800.00	0.264	-68.8	6.411	96.5	0.090	62.0	0.475	-38.3
1000.00	0.199	-70.8	5.335	87.8	0.113	61.6	0.414	-40.1
1200.00	0.158	-75.7	4.674	82.4	0.139	62.5	0.392	-42.2
1400.00	0.121	-77.9	4.068	77.5	0.157	61.1	0.377	-44.8
1600.00	0.089	-80.4	3.610	71.4	0.180	59.7	0.352	-46.6
1800.00	0.073	-82.4	3.301	67.8	0.198	59.3	0.321	-50.6
2000.00	0.052	-114.2	3.027	65.1	0.211	58.9	0.298	-52.5
2200.00	0.030	-166.0	2.724	59.9	0.228	56.0	0.286	-58.0

**NEC** 2SC5181

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